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(54) SEMICONDUCTOR DEVICE HAVING TAPERED METAL COATED SIDEWALLS

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(57)ABSTRACT

A semiconductor device includes a semiconductor die having a top side surface comprising a semiconductor material including circuitry therein having bond pads connected to nodes in the circuitry, a bottom side surface, and sidewall surfaces between the top side surface and the bottom side surface. A metal coating layer including a bottom side metal layer is over the bottom side surface that extends continuously to a sidewall metal layer on the sidewall surfaces. The sidewall metal layer defines a sidewall plane that is at an angle from 10° to 60° relative to a normal projected from a bottom plane defined by the bottom side metal layer.

